



3.7-4.0GHz, 50W, 30V GaN PA Module

Description

The GMAH3740-50 is a 50-watt peak power, integrated 2-stage Power Amplifier Module, designed for massive MIMO applications, with frequencies from 3.7 to 4GHz.

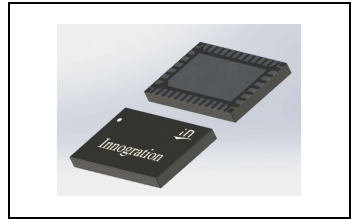
The module is 50 Ω input fully matched and output partially matched, and requires minimal external components. The module offers a much smaller footprint than traditional discrete component solutions. The module incorporates an asymmetrical Doherty final stage and its driver, delivering high power added efficiency for the entire module at 8W average power.

Compared to the closest LDMOS MMIC solution, it can support much wider bandwidth up to 300MHz and maintain at least 10% higher efficiency relatively.

Innogrations owns the patents for internal Doherty architecture, and related plastic open cavity.

• Typical Performance of Doherty Demo (On Innogrations fixture):

$V_{D1,2} = 30\text{ V}$, $I_{DQ1} = 24\text{ mA}$, $I_{DQ3} = 50\text{ mA}$, $V_{G2} = -4.2\text{ V}$.



Freq(MHz)	Pout(dBm)	CCDF(dB)	Ppeak(dBm)	Ppeak(W)	ACPR(dBc)	Gain(dB)	Efficiency(%)
3700	39.00	8.38	47.38	54.65	-30.88	29.11	48.08
3850	38.98	8.61	47.59	57.40	-29.96	29.16	47.45
4000	38.99	8.41	47.40	54.99	-30.22	30.00	48.29

Notes:

(1) WCDMA signal: 3GPP test model 1; 1 to 64 DPCH; Channel Bandwidth=3.84MHz, PAR =10.5 dB at 0.01 % probability on CCDF.

Features

- N77/N78 power amplifier
- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- 50 Ω Input fully matched
- Integrated Doherty Final Stage
- 6x10 mm Surface Mount Open plastic Package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Pin Configuration and Description





Pin No.	Symbol	Description
6	RF IN	RF Input
1	VDS-driver	Driver stage, Drain Bias
4	VGS-driver	Driver stage, Gate Bias
19,21	RF Out2	RF Output, Main Amplifier
22,24	RF Out1	RF Output, Peaking Amplifier
11	VGS-main	Main Amplifier, Gate Bias
16,17	VDS-main	Main Amplifier, Drain Bias
32	VGS-peak	Peaking Amplifier, Gate Bias
26,27	VDS-Peak	Peaking Amplifier, Drain Bias
3,8-10,14,15,28,29,33-35	NC	No connection
2,5,7,12,13,18,20,23,25,30,31,36	GND	Internal Grounding, recommend connecting to Epad ground
Package Base	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	15	Vdc
Gate--Source Voltage	V_{GS}	-10 to +1	Vdc
Operating Voltage	V_{DD}	+40	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_c	+150	°C
Operating Junction Temperature	T_j	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance@Average Power, Junction to Case $T_{case}=+85^{\circ}C$, CW Test, $P_{diss}=9W$, $P_{out}=8W$,	$R_{\theta JC}$	TBD	°C/W

Notes:

- (1) The thermal resistance is acquired by our company’s FEA model, which was calibrated by IR measurement, the value shall be applied to reliability.
- (2) The reference T_{case} temperature $85^{\circ}C$ is apply on the backside of package.
- (3) The device soldering onto the 20mil Rogers PCB with $50 \times \Phi 0.4mm$ via hole beneath the package backside and the reference temperature T_{case} ($85^{\circ}C$) apply on the groundside of the PCB.
- (4) The power dissipation in the table is overall dissipation which include Carrier PA, Peaking PA and driver PA.

Table 3. ESD Protection Characteristics

Test Methodology	Class Voltage
Human Body Model(HBM) (JEDEC Standard JESD-A114)	$\pm 225V$
Charged Device Model (CDM) (JEDEC Standard JESD22-C101F)	$\pm 1000V$

Load Mismatch of per Section (On Test Fixture, 50 ohm system): $V_{D1,2}=28V$, $I_{DQ1}=24mA$, $I_{DQ3}=50mA$, $V_{G2}=-4V$, $f=3.7GHz$

VSWR 10:1 at P3dB pulse CW Output Power	No Device Degradation
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TYPICAL CHARACTERISTICS

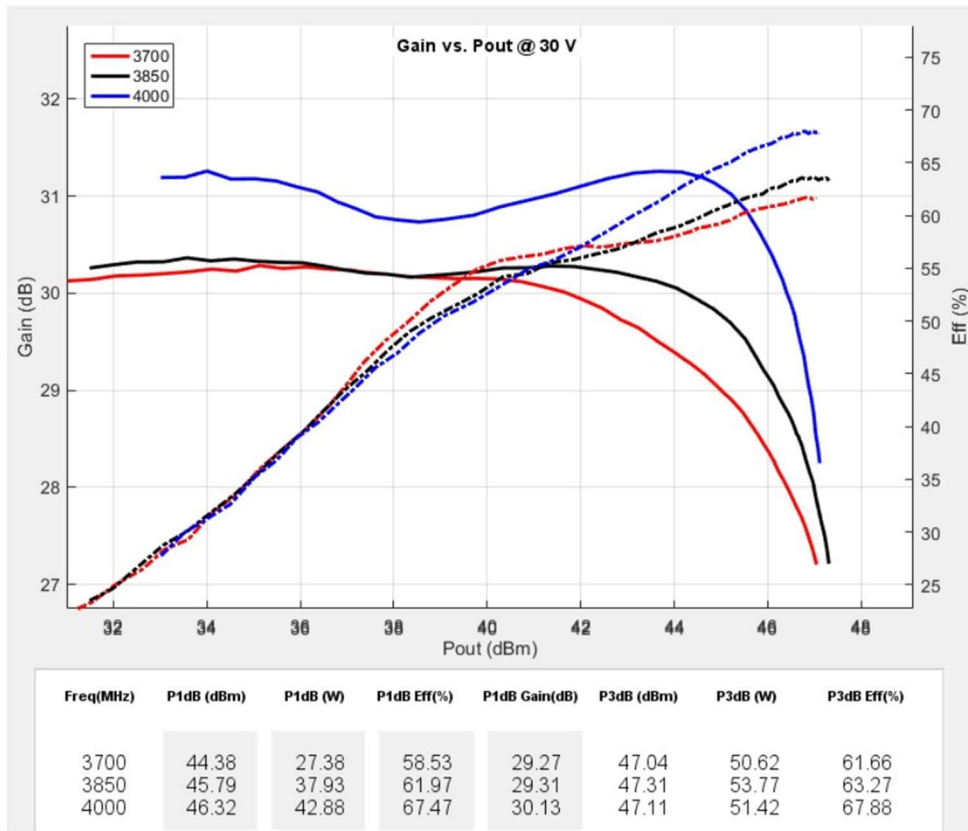


Figure 1. Power Gain and Drain Efficiency as Function of Pulse Output Power

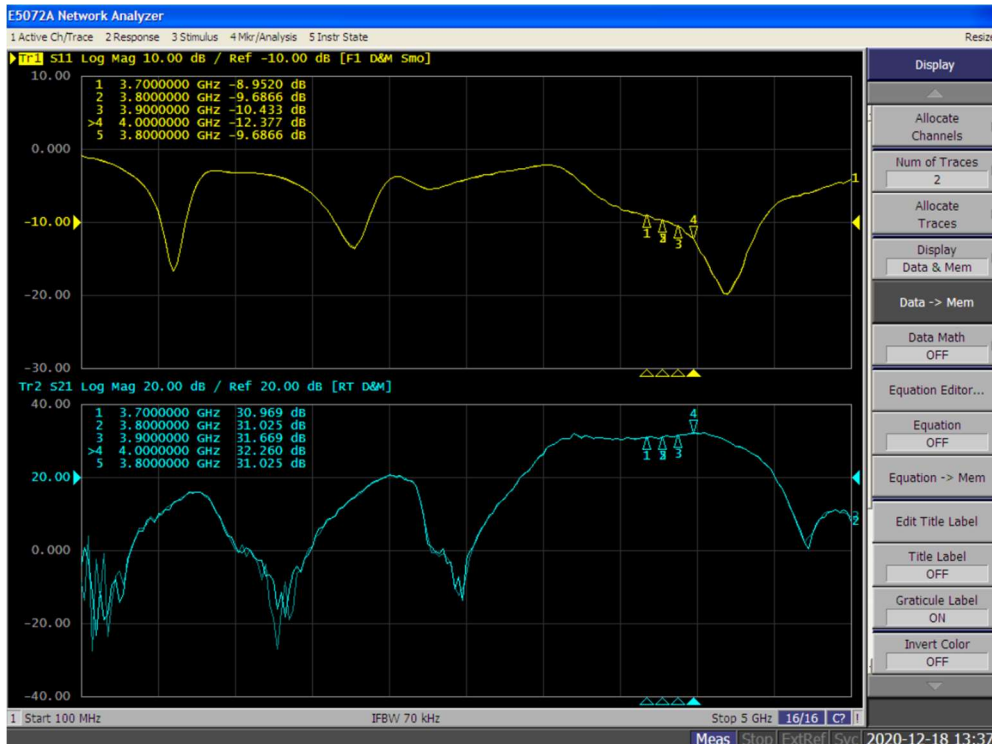


Figure 3. Network analyzer output S11/S21



Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2020/10/18	Rev 1.0	Preliminary Datasheet

Application data based on LWH-20-41

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